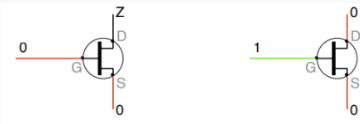
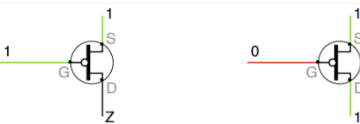
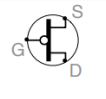


Technologie CMOS (complementary metal-oxide semiconductor) -> procédé de fabrication de transistor / effet de champ (MOFSET metal oxide semiconductor) / tech planaire (implanté à la surface du silicium)

> Transistor NMOS

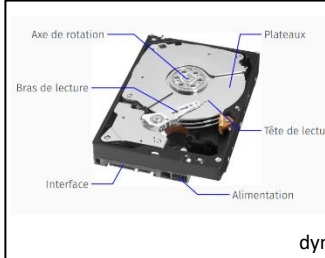


> Transistor PMOS



D « gain » ; G « grille » ; S « source »

Disque dur :



HDD : hard disk drive

SDD : Solid state drive

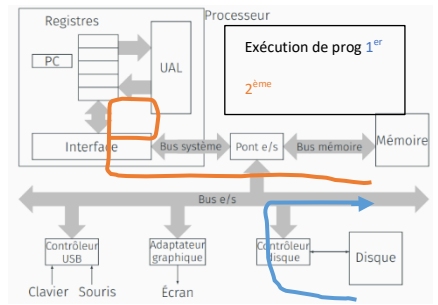
Mémoire vive : DRAM :
dynamic Random Access Memory

Bit (binary digit) :

Une valeur logique pouvant prendre deux états : 0 ou 1

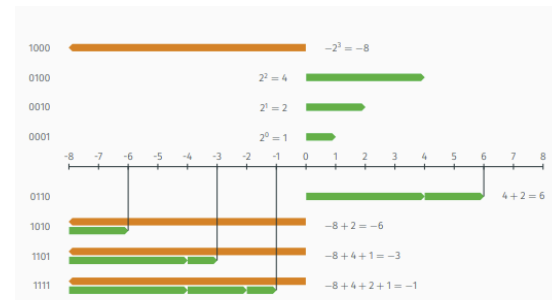
DECIMAL	HEX	BINARY
0	0	0000
1	1	0001
2	2	0010
3	3	0011
4	4	0100
5	5	0101
6	6	0110
7	7	0111
8	8	1000
9	9	1001
10	A	1010
11	B	1011
12	C	1100
13	D	1101
14	E	1110
15	F	1111

2^{-n}	n	2^n
1	0	1
0.5	1	2
0.25	2	4
0.125	3	8
0.0625	4	16
0.03125	5	32
0.015625	6	64
0.0078125	7	128
0.00390625	8	256
0.001953125	9	512
0.0009765625	10	1024

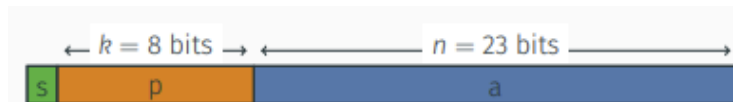


Nom	Symbole	En octets	En bits
bit	b	-	1
octet	B	1	8
Kibioctet	KiB	2^{10}	2^{13}
Mébioctet	MiB	2^{20}	2^{23}
Gibioctet	GiB	2^{30}	2^{33}
Tébioctet	TiB	2^{40}	2^{43}
Kilooctet	KB	10^3	8×10^3
Mégaoctet	MB	10^6	8×10^6
Gigaoctet	GB	10^9	8×10^9
Téraoctet	TB	10^{12}	8×10^{12}

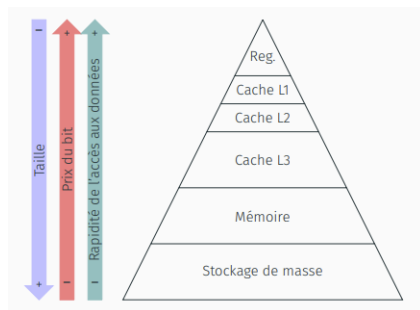
Complément à 2



Le format IEEE 754 :



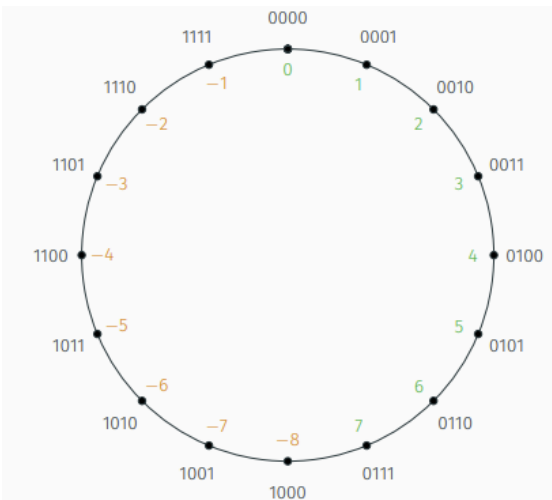
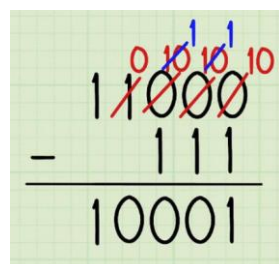
Hierarchie de la mémoire :



Addition :

table d'addition
0 + 0 = 0
0 + 1 = 1
1 + 0 = 1
1 + 1 = 10 (on pose 0 et on retient 1)
1 + 1 = 11 (on pose 1 et on retient 1)

Soustraction : $-x = \overline{x} + 1$



$1001_2 = 9$

$1001_{C2} = -7$

Si 1 0101 comme sur 4 bits = 0101

Sur 8 bits = de -128 à 127

Ex en Cà2 : 1000 0000 = -128